

TN3440A



NPN General Purpose Amplifier

This device is designed for use in horizontal driver, class A off-line amplifier and off-line switching applications. Sourced from Process 36.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	250	V	
V _{CBO}	Collector-Base Voltage	300	V	
V _{EBO}	Emitter-Base Voltage	7.0	V	
I _C	Collector Current - Continuous	100	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		TN3440A		
P_D	Total Device Dissipation Derate above 25°C	1.0 8.0	W mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	50	°C/W	

NPN General Purpose Amplifier

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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
V _{CEO(sus)}	Collector-Emitter Sustaining Voltage*	I _C = 50 mA, I _B = 0	250		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, I_E = 0$	300		V
I _{CEO}	Collector-Cutoff Current	V _{CE} = 200 V, I _B = 0		50	μА
I _{CEX}	Collector-Cutoff Current	V _{CE} = 300 V, V _{BE} = 1.5 V		500	μА
I _{CBO}	Collector-Cutoff Current	V _{CB} = 250 V, I _E = 0		20	μА
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_{C} = 0$		20	μА
ON CHAR	ACTERISTICS DC Current Gain	I _C = 2.0 mA, V _{CE} = 10 V	30		
		$I_C = 20 \text{ mA}, V_{CE} = 10 \text{ V}$	40	160	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_{\rm C}$ = 50 mA, $I_{\rm B}$ = 4.0 mA		0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 50 mA, I _B = 4.0 mA		1.3	V
SMALL SI	GNAL CHARACTERISTICS				
f⊤	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ f = 5.0 MHz	15		MHz
C _{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		10	pF

 $V_{BE} = 5.0 \text{ V}, I_{C} = 0, f = 1.0 \text{ MHz}$

 $I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V},$

f = 1.0 kHz

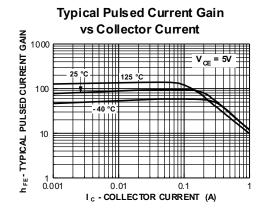
Input Capacitance

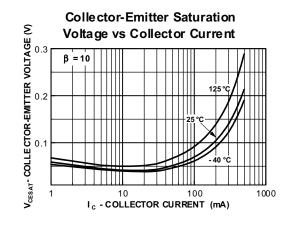
Small-Signal Current Gain

 $C_{ibo} \\$

h_{fe}

Typical Characteristics



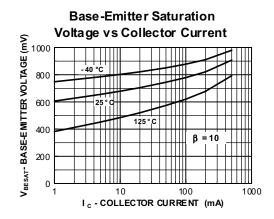


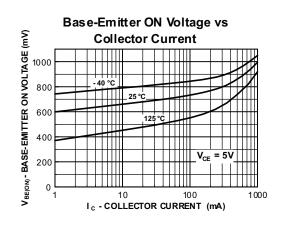
^{*}Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 1.0%

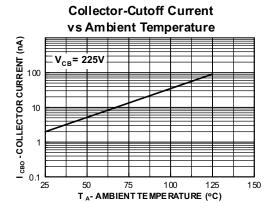
NPN General Purpose Amplifier

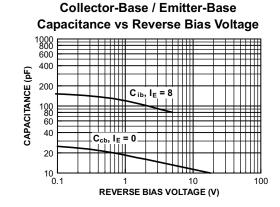
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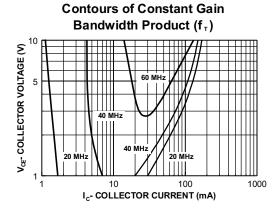
Typical Characteristics (continued)

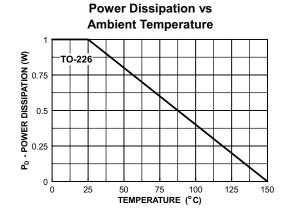


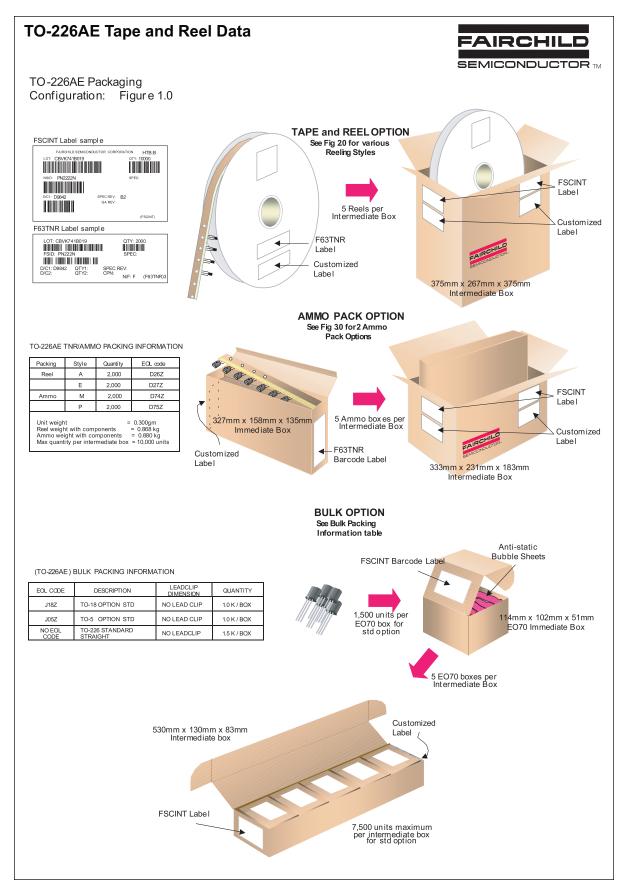








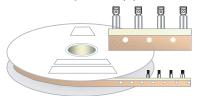




TO-226AE Tape and Reel Data, continued

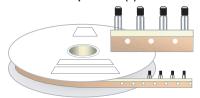
TO-226AE Reeling Style Configuration: Figure 2.0

Machine Option "A" (H)



Style "A" D26Z, D70Z (s/h)

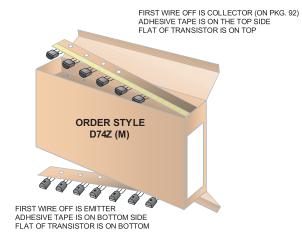
Machine Option "E"(J)



Style "E" D27Z, D71Z (s/h)

TO-226AE Radial Ammo Packaging

Configuration: Figure 3.0



FIRST WIRE OFF IS EMITTER (ON PKG. 92)
ADHESIVE TAPE IS ON THE TOP SIDE
FLAT OF TRANSISTOR IS ON BOTTOM

ORDER STYLE
D75Z (P)

FIRST WIRE OFF IS COLLECTOR ADHESIVE TAPE IS ON BOTTOM SIDE FLAT OF TRANSISTOR IS ON TOP

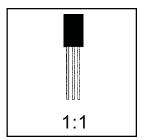
TO-226AE Tape and Reel Data, continued TO-226AE Tape and Reel Taping Dimension Configuration: Figure 4.0 ITEM DESCRIPTION SYMBOL DIMENSION Base of Package to Lead Bend 0.098 (max) Component Height Hb 1.078 (+/- 0.050) User Direction of Feed Lead Clinch Height 0.630 (+/- 0.020) HO Component Base Height H1 0.748 (+/- 0.020) Component Alignment (side/side) Pd 0.040 (max) 0.031 (max) Component Alignment (front/back) Hd Component Pitch 0.500 (+/- 0.020) РО Feed Hole Pitch 0.500 (+/- 0.008) Hole Center to First Lead P1 0.150 (+0.009, -0.010) Hole Center to Component Center P2 0.247 (+/- 0.007) Lead Spread F1/F2 0.104 (+/- 0 010) Lead Thickness d 0.018 (+0.002, -0.003) 0.429 (max) Cut Lead Length L1 0.209 (+0.051, -0.052) Taped Lead Length Taped Lead Thickness 0.032 (+/- 0.006) Carrier Tape Thickness t1 0.021 (+/- 0.006) TO-226AE Reel 0.708 (+0.020, -0.019) Carrier Tape Width W Configuration: Figure 5.0 Hold - down Tape Width wo 0.236 (+/- 0.012) 0.035 (max) Hold - down Tape position W1 0.360 (+/- 0.025) Feed Hole Position W2 0.157 (+0.008, -0.007) DO Sprocket Hole Diameter Lead Spring Out S 0.004 (max) Note: All dmensions are in inches. D4 ITEM DESCRIPTION SYMBOL MINIMUM MAXIMUM Red Diameter 13975 14.025 Arbor Hole Diameter (Standard) 1.160 1.200 D2 D2 0.650 0.700 (Small Hole) Core Diameter D3 3.100 3.300 Hub Recess Inner Diameter 2.700 3.100 D4 Hub Recess Depth W 1 0.370 0.570 Range to Range Inner Width 1.630 Hub to Hub Center Width 2.090 Note: All dimensions are inches

TO-226AE Package Dimensions



TO-226AE (FS PKG Code 95, 99)

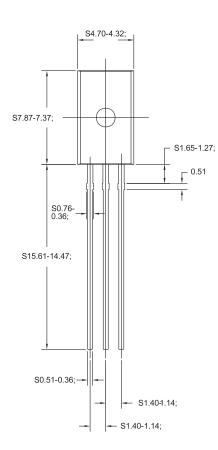


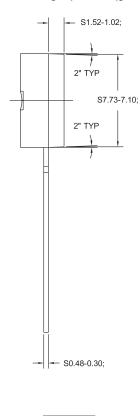


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.300







99 95 1 E E 2 B C 3 C B TO-226AE (95,99)

For leadformed option ordering, refer to Tape & Reel data information.

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